Electronic Supporting Information

A Facile Process to Achieve Hysteresis-free and Fully Stabilized Graphene Field-effect Transistors

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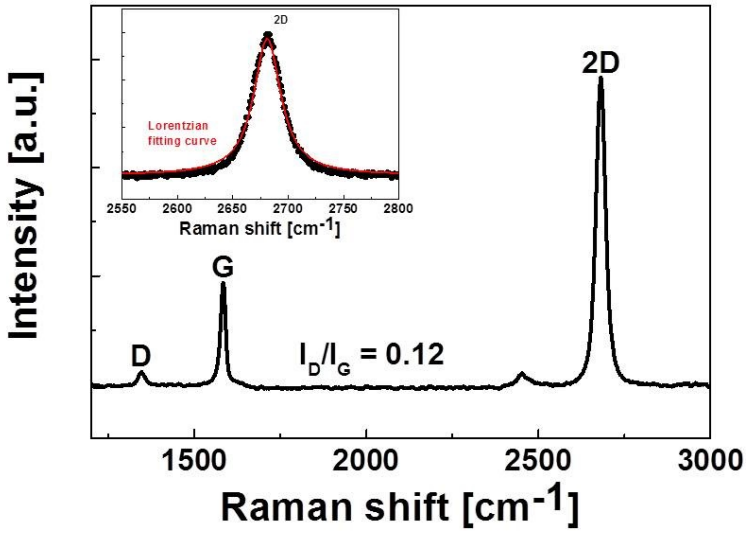

Fig. S1 Raman spectrum of single layer graphene grown by CVD after transfer process. The insert figure shows 2D peak which was fitted by Lorentz curve. Also in this case I_D/I_G, which indicates the quality of graphene, is about 0.12

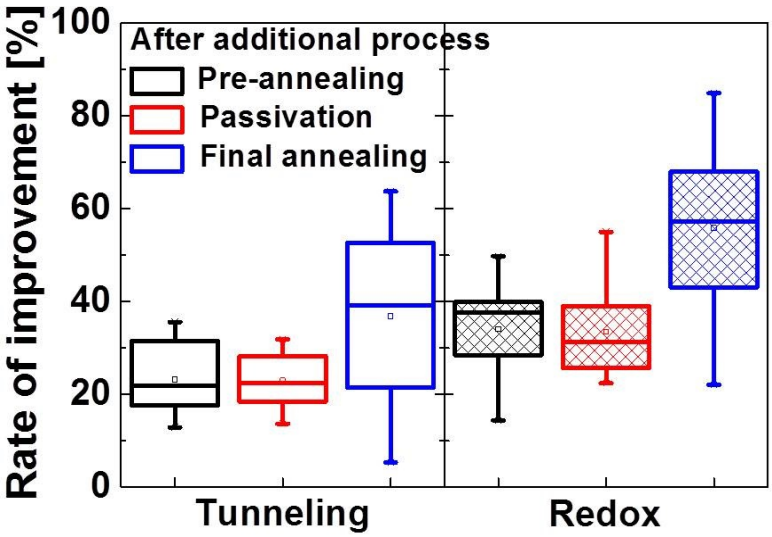

Fig. S2 Rate of improvement related tunneling and redox charge density on the basis of previous process. Through final annealing, tunneling and redox charge density decrease drastically.